

1. General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO-92) plastic package.

2. Features and benefits

- Fast switching
- High typical DC current gain
- High voltage capability of 700 V
- Very low switching and conduction losses

3. Applications

- Compact fluorescent lamps (CFL)
- Low power electronic lighting ballasts
- Off-line self-oscillating power supplies (SOPS) for battery charging

4. Quick reference data

Table 1. Quick	reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _C	collector current	DC	-	-	1.5	А
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>	-	-	2.1	W
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	-	700	V
Static characte	eristics					
h _{FE}	DC current gain	I_{C} = 0.5 A; V_{CE} = 2 V; T_{lead} = 25 °C	8	17	25	
		I_C = 1 A; V_{CE} = 2 V; T_{lead} = 25 °C	5	9	15	

5. Pinning information

Table 2. F	Pinning inf	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	С	collector		в
3	E	emitter		E sym123
			TO-92 (SOT54)	· · · · ·

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PHE13003C	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	700	V
V _{CBO}	collector-base voltage	I _E = 0 A	-	700	V
V _{CEO}	collector-emitter voltage	I _B = 0 A	-	400	V
V _{EBO}	emitter-base voltage	I _C = 0 A; I(Emitter) = 10 mA	-	9	V
I _C	collector current	DC	-	1.5	А
I _{CM}	peak collector current		-	3	А
I _B	base current	DC	-	0.75	А
I _{BM}	peak base current		-	1.5	А
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>	-	2.1	W
T _{stg}	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C

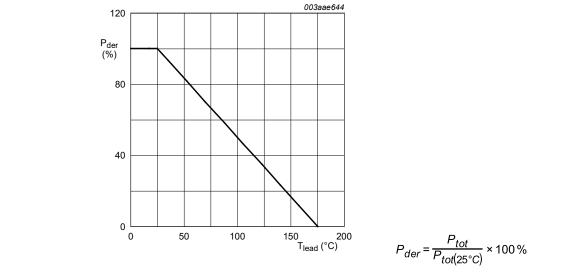
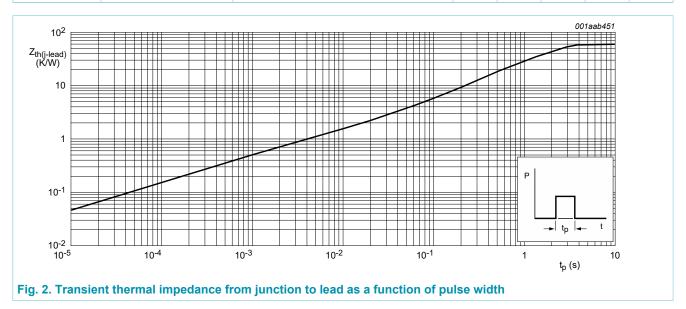


Fig. 1. Normalized total power dissipation as a function of lead temperature



8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	Fig. 2	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air; printed circuit board mounted; lead length = 4 mm	-	150	-	K/W



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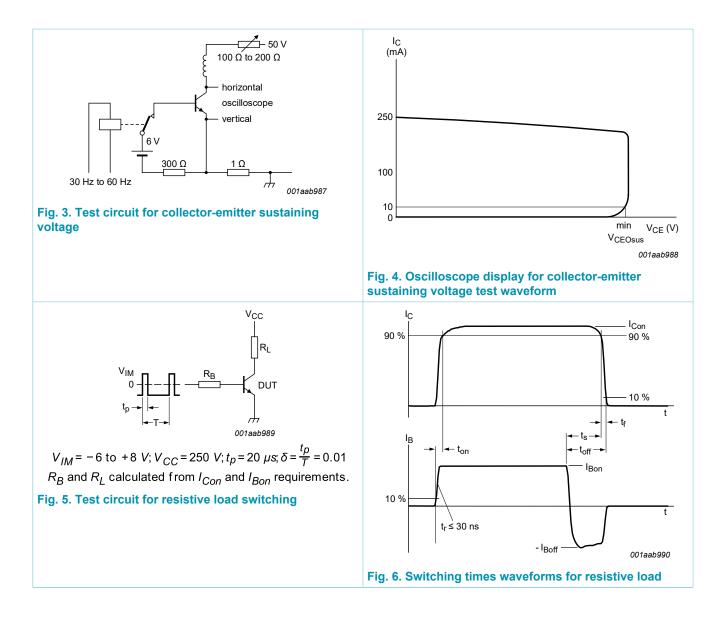
9. Characteristics

Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
Static chara	cteristics	·					
I _{CES}	collector-emitter cut-off	V_{BE} = 0 V; V_{CE} = 700 V; T_j = 125 °C	-		-	5	mA
	current (base shorted)	V_{BE} = 0 V; V_{CE} = 700 V; T_j = 25 °C	-		-	1	mA
I _{CEO}	collector-emitter cut-off current (base open)	V_{CE} = 400 V; I _B = 0 A; T _{lead} = 25 °C	-		-	0.1	mA
ЕВО	emitter-base cut-off current (collector open)	V_{EB} = 9 V; I _C = 0 A; T _{lead} = 25 °C	-		-	1	mA
V _{CEOsus}	collector-emitter sustaining voltage (base open)	I _B = 0 A; I _C = 1 mA; L _C = 25 mH; T _{lead} = 25 °C; <u>Fig. 3</u> ; <u>Fig. 4</u>	4	00	-	-	V
V _{CEsat}	collector-emitter	I _C = 0.5 A; I _B = 0.1 A; T _{lead} = 25 °C	-		-	0.5	V
	saturation voltage	I_{C} = 1 A; I_{B} = 0.25 A; T_{lead} = 25 °C	-		-	1	V
		I_C = 1.5 A; I_B = 0.5 A; T_{lead} = 25 °C	-		-	1.5	V
V _{BEsat}	base-emitter saturation	$\rm I_C$ = 0.5 A; $\rm I_B$ = 0.1 A; $\rm T_{lead}$ = 25 °C	-		-	1	V
	voltage	I_{C} = 1 A; I_{B} = 0.25 A; T_{lead} = 25 °C	-		-	1.2	V
h _{FE}	DC current gain	I_C = 0.5 A; V_{CE} = 2 V; T_{lead} = 25 °C	8		17	25	
		I_C = 1 A; V_{CE} = 2 V; T_{lead} = 25 °C	5		9	15	
Dynamic ch	aracteristics						
t _{on}	turn-on time	$I_{C} = 1 \text{ A}; I_{Bon} = 0.2 \text{ A}; I_{Boff} = -0.2 \text{ A};$	-		-	1	μs
t _s	storage time	R_L = 75 Ω; T_{lead} = 25 °C; resistive load; Fig. 5; Fig. 6	-		-	4	μs
		$\begin{split} I_C &= 1 \text{ A}; \ I_{Bon} = 0.2 \text{ A}; \ V_{BB} = -5 \text{ V}; \\ L_B &= 1 \ \mu\text{H}; \ T_{lead} = 25 \ ^\circ\text{C}; \ \text{inductive load}; \\ \hline \text{Fig. 7}; \ \hline \text{Fig. 8} \end{split}$	-		0.8	-	μs
t _f	fall time	$ I_C = 1 \text{ A}; I_{Bon} = 0.2 \text{ A}; I_{Boff} = -0.2 \text{ A}; \\ R_L = 75 \Omega; T_{lead} = 25 \text{ °C}; \text{ resistive load}; \\ \hline Fig. 5; Fig. 6 $	-		-	0.7	μs
		$\begin{split} I_{C} &= 0.5 \text{ A}; \ I_{Bon} = 0.1 \text{ A}; \ V_{BB} = -5 \text{ V}; \\ I_{B} &= 1 \ \mu\text{H}; \ T_{lead} = 25 \ ^{\circ}\text{C}; \ \text{inductive load}; \\ \hline \text{Fig. 7}; \ \hline \text{Fig. 8} \end{split}$	-		0.1	-	μs

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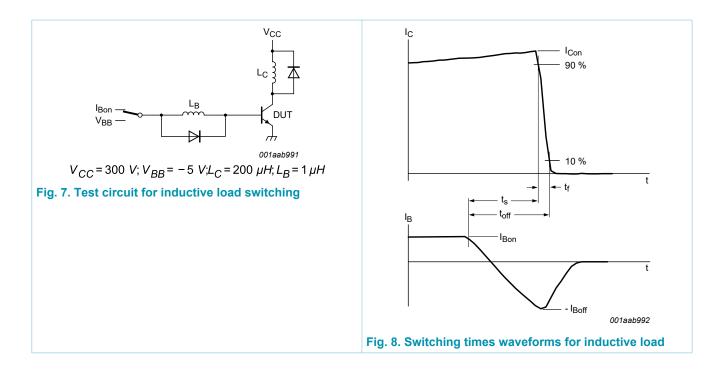
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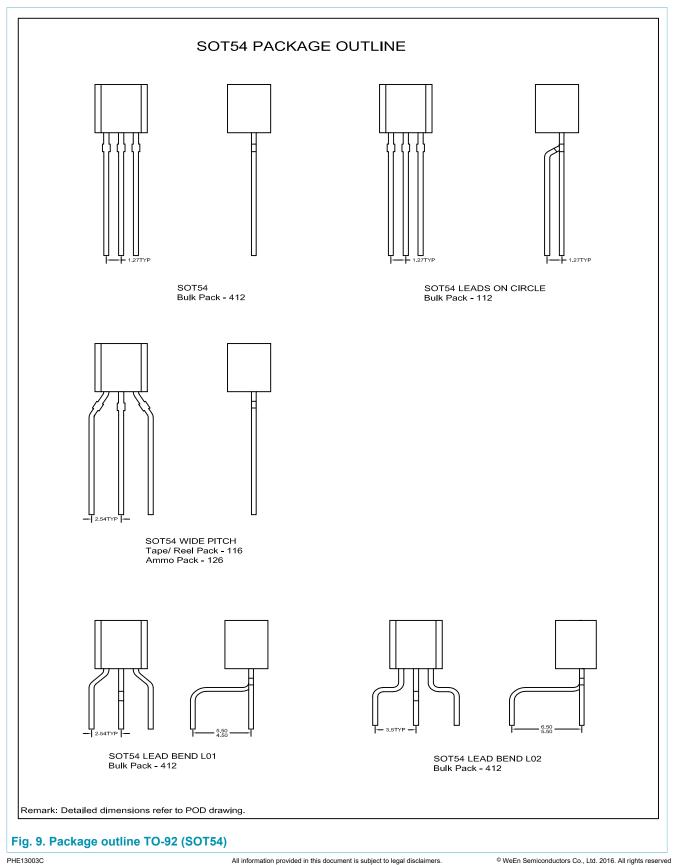
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10. Package outline



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Document status [1][2]	Product status [<u>3]</u>	Definition
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